## **2018 14th IEEE International Conference on Solid-State** and Integrated Circuit **Technology (ICSICT 2018)**

Qingdao, China 31 October - 3 November 2018

Pages 1-726



**IEEE Catalog Number: CFP18829-POD ISBN**:

978-1-5386-4442-3

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IEEE Catalog Number: CFP18829-POD ISBN (Print-On-Demand): 978-1-5386-4442-3 ISBN (Online): 978-1-5386-4441-6

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